

- Claim 23: (Added) The layered material of claim 21, wherein the line dielectric layer comprises an organic low dielectric constant material.
- Claim 24: (Added) The layered material of claim 23, wherein the organic low dielectric constant material is selected from the group consisting of a polyarylene ether, a polyarylene, a polyimide, and cyanate ester resin.
- Claim 25: (Added) The layered material of claim 21, wherein application of the hard mask in liquid phase comprises a spin-on process.
- Claim 26: (Added) The layered material of claim 21, wherein the hard mask layer is formed from a polyperhydrosilazane.
- Claim 27: (Added) The layered material of claim 27, wherein the polyperhydrosilazane has a structure represented by  $(\text{SiH}_2\text{-NH})_n$ , wherein n is an integer between 2 and 2000.
- Claim 28: (Added) The layered material of claim 21, wherein the hard mask layer is densified using a process selected from the group consisting of a furnace cure process, a rapid thermal anneal process, a hot plate anneal process, and an electron beam process.
- Claim 29: (Added) The layered material of claim 21, further comprising a diffusion barrier layer.
- Claim 30: (Added) The layered material of claim 29, wherein the diffusion barrier layer is applied in a liquid phase to the hard mask layer.
- Claim 31: (Added) The layered material of claim 29, wherein the diffusion barrier comprises a Si-N bond.